

Low Noise Amplifier Chip

AAS2215

Product Specification

V1.0

1. Product Features

Frequency Range: 14~18 GHz

Small Signal Gain: 31 dB

Noise Figure: 0.9 dB

Output P1dB (OP1dB): 5 dBm

Input P1dB (IP1dB): -25 dBm

Bias Conditions: VC = 5V, IDQ = 13mA

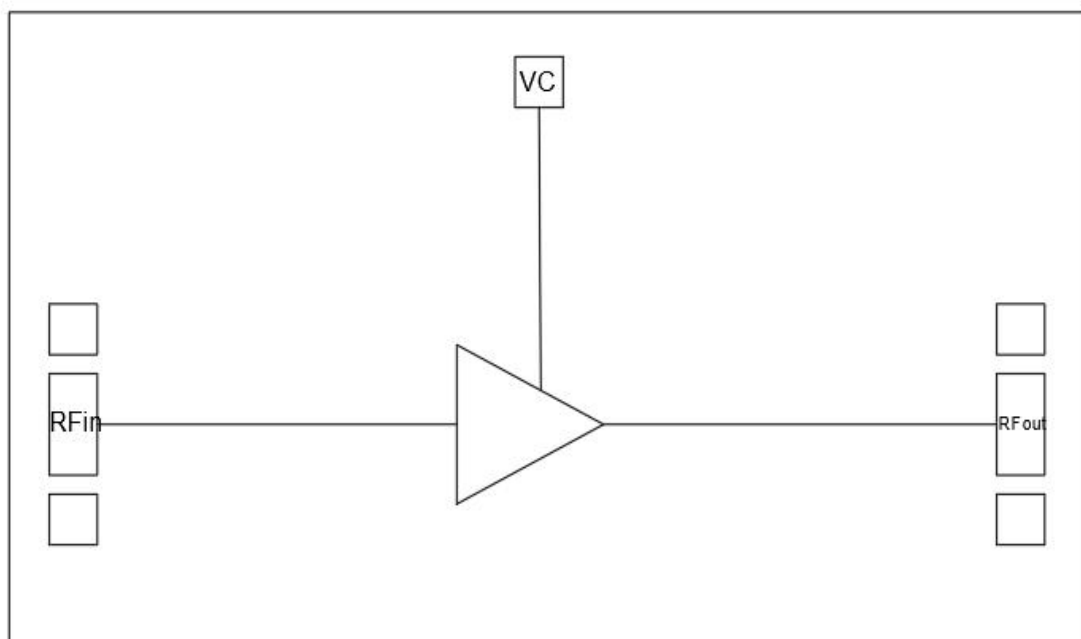
Chip Dimensions: 2mm×0.7mm×0.1mm

2. Functional Overview

This chip is a low noise amplifier operating in the 14~18 GHz frequency band, powered by a +5V supply. At an operating current of 13mA, it provides a small signal gain of 31 dB with an output P1dB of 5 dBm and a typical noise figure of 0.9 dB.

DC blocking capacitors are integrated at all RF ports of the chip, with a port impedance of 50Ω. The chip adopts backside metal grounding design.

3. Block Diagram



4. Typical Applications

Applicable to communication, radar and other related fields.

5. Electrical Characteristics

5.1 RF Characteristics

Unless otherwise specified, all electrical parameters are measured under the following conditions: $V_C = 5.0V$, $I_{DQ} = 13mA$, small signal input power $P_{in} = -25dBm$, ambient temperature $T_A = +25^\circ C$, 50Ω system, continuous wave signal.